

DMC501E0

Silicon NPN epitaxial planar type

For High frequency amplification
DMC201E0 in SMini5 type package

■ Features

- High transition frequency f_T
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DSC2F01X (Common Emitter)

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

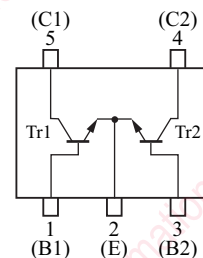
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	15	V
Collector-emitter voltage (Base open)	V_{CEO}	10	V
Emitter-base voltage (Collector open)	V_{EBO}	3	V
Collector current	I_C	50	mA
Total power dissipation	P_T	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code
SMini5-F3-B
- Pin Name
1: Base (Tr1) 4: Collector (Tr2)
2: Emitter (Common) 5: Collector (Tr1)
3: Base (Tr2)

■ Marking Symbol: C7

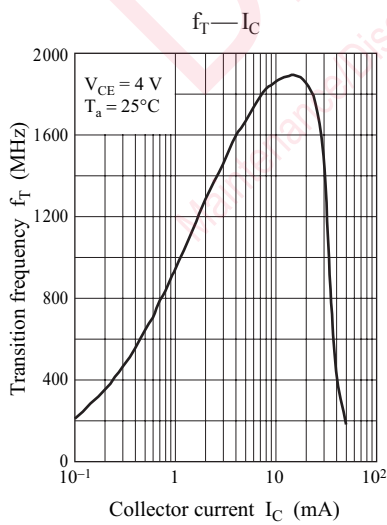
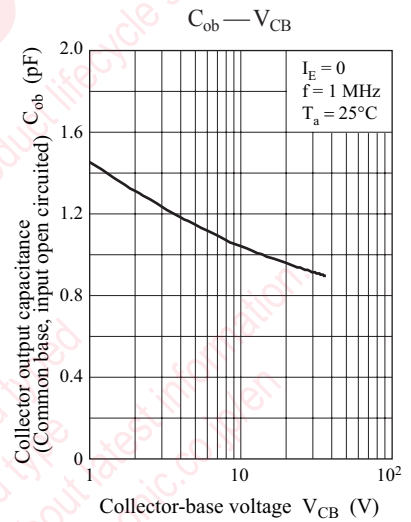
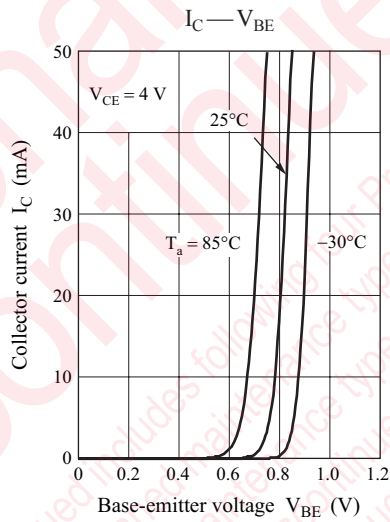
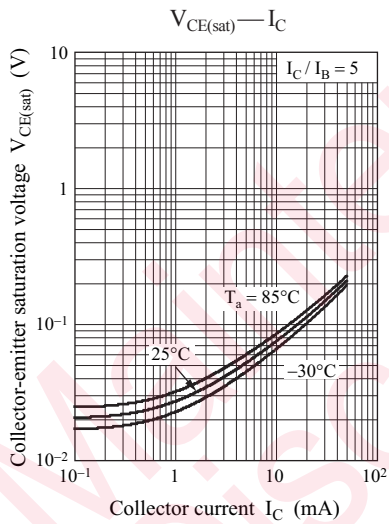
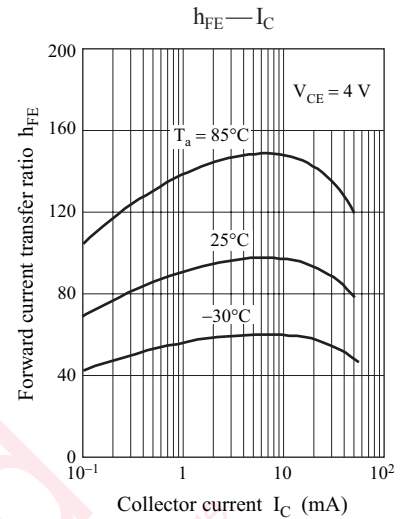
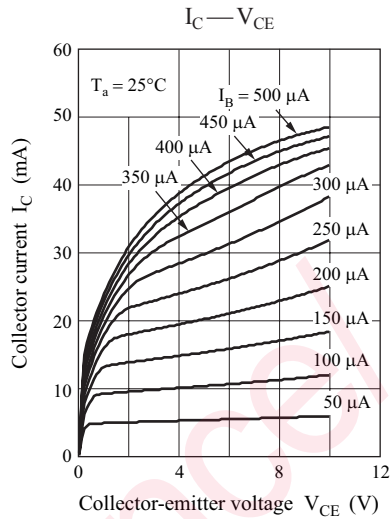
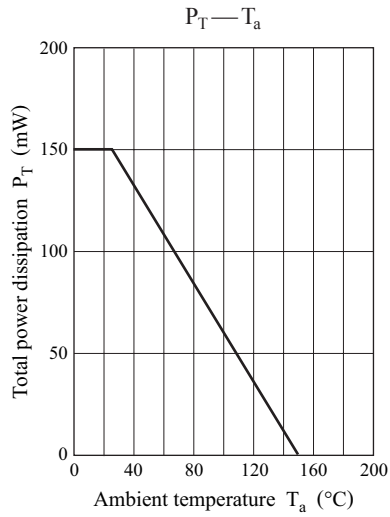
■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

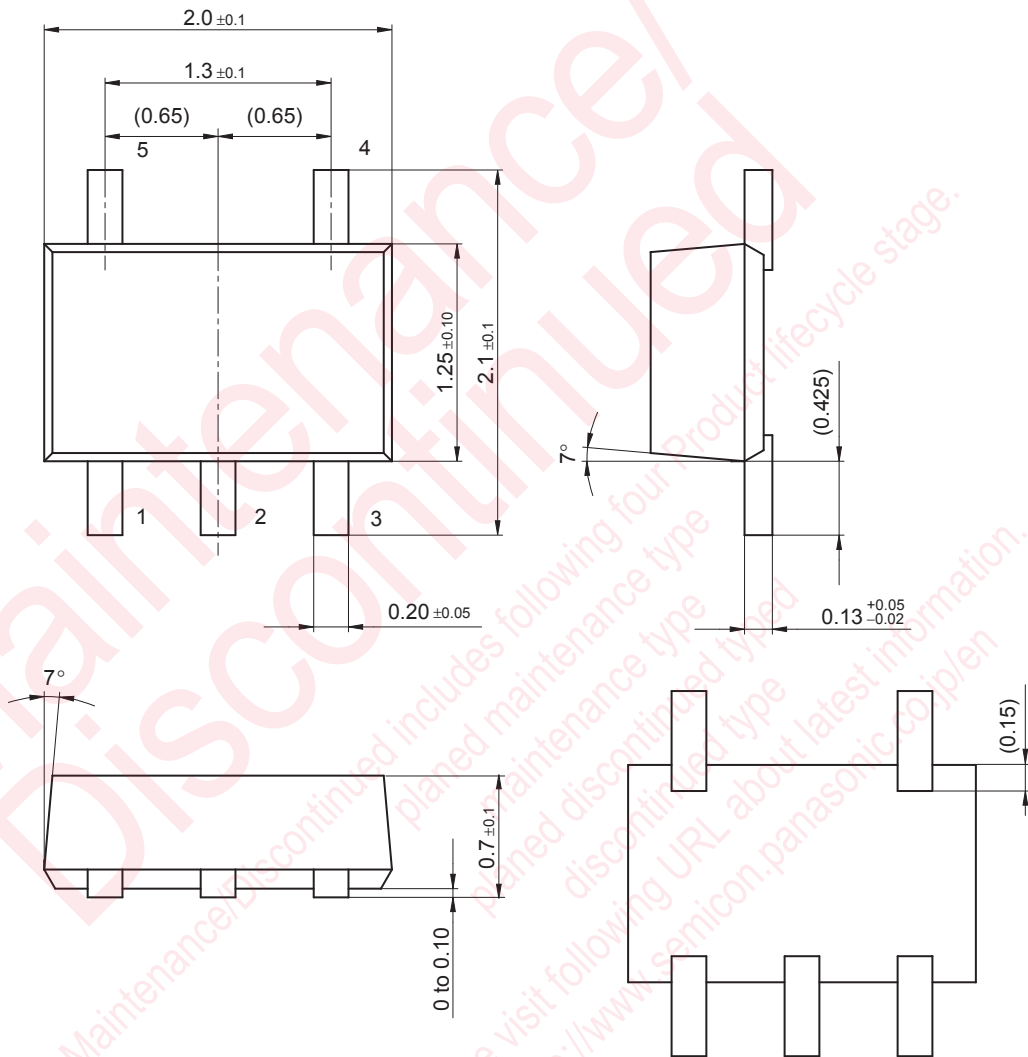
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	10			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	3			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10 \text{ V}, I_E = 0$			1	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 4 \text{ V}, I_C = 5 \text{ mA}$	75		220	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$			0.5	V
Transition frequency	f_T	$V_{CE} = 4 \text{ V}, I_C = 5 \text{ mA}$		1.9		GHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 4 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.2		pF
Collector-base parameter	$r_{bb}' \cdot C_C$	$V_{CE} = 4 \text{ V}, I_C = 5 \text{ mA}, f = 31.9 \text{ MHz}$		12		ps
Reverse transfer capacitance (Common base)	C_{rb}	$V_{CE} = 4 \text{ V}, I_C = 0, f = 1 \text{ MHz}$		0.6		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SMini5-F3-B

Unit: mm



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